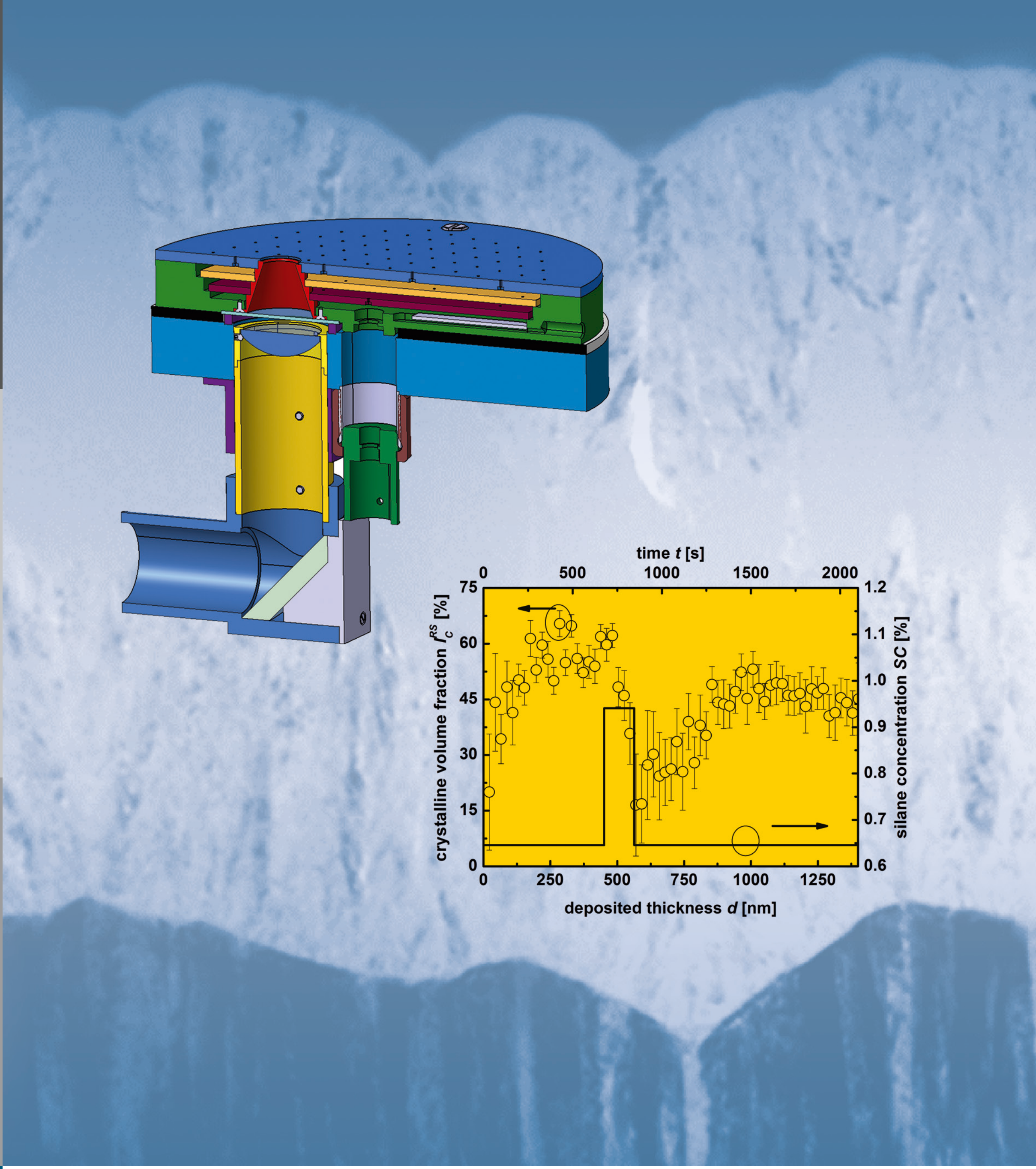

In-Situ Raman Spectroscopy: A Method to Study and Control the Growth of Microcrystalline Silicon for Thin-Film Solar Cells

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